TRANSISTORS, HIGH POWER, NPN

BASED ON TYPE 2N3767

ESCC Detail Specification No. 5203/027

ISSUE 1

October 2002

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space components
coordination group

Issue/Rev.	Date	Approved by	
		SCCG Chairman	ESA Director General or his Deputy
Issue 2	December 1985	-	
Revision 'A'	February 1992		

DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	Reference	CHANGE Item	Approved DCR No.
		This Issue supersedes Issue 1 and incorporates all modifications agreed on the basis of the following DCR's:-		
		Table of Contents	: Reference to Appendices added	21019
			: Reference to Tables 1(a) and 1(b) added	21021
		Para. 1.2	: New text	21021
		Para. 1.3	: Reference to Table 1(b) added	21021
		Para. 2	: Transferred from Page 9	None
		Table 1(a)	: Added	21021
		Table 1	: Renumbered as Table 1(b)	21021
		Para. 2	: MIL-STD-1276 deleted	21025
		Para. 4.1	: Reference to Appendices added	21019
		Para. 4.2.2	: Requirement added for Bond Strength and Die Shear tests	21022
		Para. 4.2.3	: Radiographic Inspection added	21022
		Para. 4.2.4	: Requirement added for Bond Strength and Die Shear tests	21022
		Para. 4.4.2	: Text rewritten	21025
		Para. 4.5.3	: Component number modified	21021
		Table 3	: Sample basis LTPD 7 specified	21022
			: Item 1: - V_{CE} changed to 100V	22350
			- Unit changed to mA	22350
		Table 4	: Item 1: - Unit changed to μA	22350
'A'	Feb. '92	P1. Cover page		None
		P2. DCN		None
		P5. Para. 2	: "ESA/SCC Basic Spec. No. 23500" added	21025
		P9. Para. 4.2.2	: PIND deviation deleted	21043
			: Bond Strength and Die Shear Test deviations deleted	23499
		Para. 4.2.3	: Radiographic Inspection deviation deleted	21049
		Para. 4.2.4	: Bond Strength and Die Shear Test deviations deleted	23499
		P15. Table 3	: Note 1 deleted, subsequent Note renumbered	21047
		This document has been transferred from hardcopy to electronic format. The content is unchanged but minor differences in presentation exist.		

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TABLES

FIGURES

APPENDICES (Applicable to specific Manufacturers only)
None.

1. GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics, test and inspection data for a Transistor, High Power, NPN, based on Type 2N3767.

It shall be read in conjunction with ESA/SCC Generic Specification No. 5000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

See Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the transistors specified herein, are scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

The derating information applicable to the transistors specified herein is shown in Figure 1.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the transistors specified herein are shown in Figure 2.

1.6 FUNCTIONAL DIAGRAM

The functional diagram showing lead identification, of the transistors specified herein, is shown in Figure 3.

2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

(a) ESA/SCC Generic Specification No. 5000 for Discrete Semiconductor Components.

(b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.

(c) ESA/SCC Basic Specification No. 23500, Requirements for Lead Materials and Finishes for Components for Space Application.

TABLE 1(a) - TYPE VARIANTS

VARIANT	BASED ON TYPE	LEAD MATERIAL AND FINISH
01	2N3767	D2

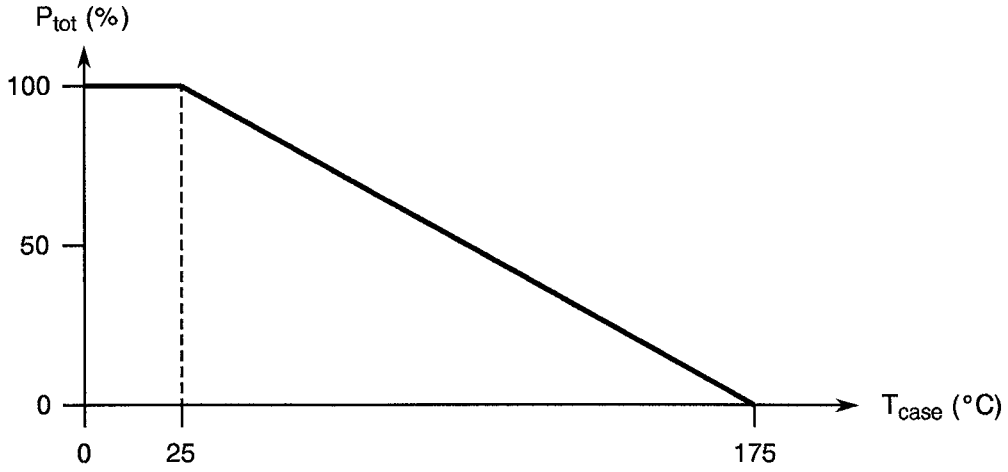
TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100	V	
2	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80	V	
3	Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	V	
4	Collector Current	I_C	4.0	A	Continuous Peak
5	Base Current (Continuous)	I_B	2.0	A	
6	Thermal Resistance	$R_{TH(J-C)}$	7.5	°C/W	
7	Power Dissipation	P_{tot}	20	W	Note 1
8	Operating Temperature Range	T_{op}	−65 to +175	°C	T_{amb}
9	Storage Temperature Range	T_{stg}	−65 to +175	°C	
10	Soldering Temperature	T_{sol}	+265	°C	Time: ≤10s Distance from case ≥1.5mm

NOTES

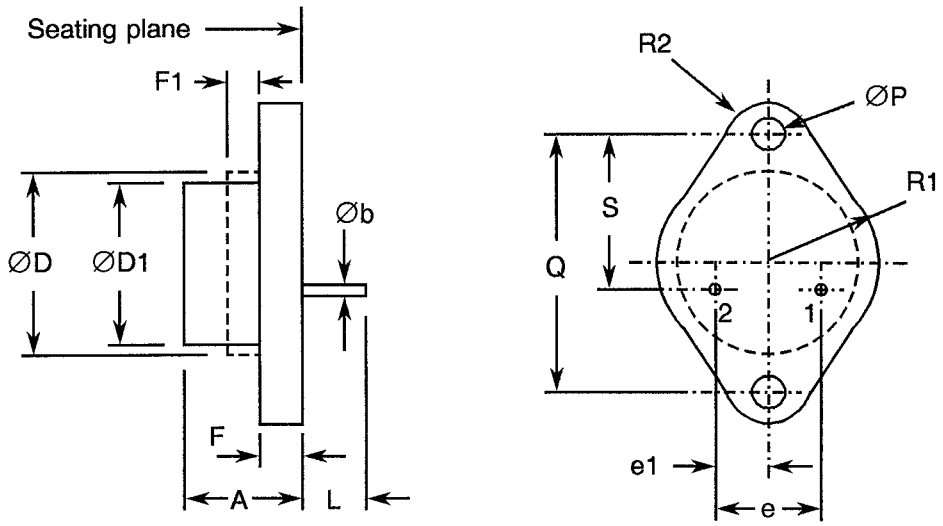
1. At $T_{case} \leq +25°C$. For derating at $T_{case} > +25°C$, see Figure 1.

FIGURE 1 - PARAMETER DERATING INFORMATION



Rated Power Dissipation versus Case Temperature

FIGURE 2 - PHYSICAL DIMENSIONS

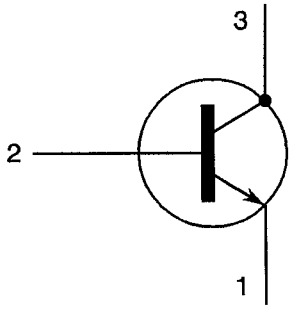


SYMBOL	INCHES		MILLIMETRES		REMARKS
	MIN.	MAX.	MIN.	MAX.	
A	0.250	0.340	6.35	8.64	
Øb	0.028	0.034	0.711	0.863	
ØD	-	0.620	-	15.75	
ØD1	0.470	0.500	11.94	12.70	
e	0.190	0.210	4.83	5.33	
e1	0.093	0.107	2.36	2.72	
F	0.050	0.075	1.27	1.91	1
F1	-	0.050	-	1.27	2
L	0.360	-	9.14	-	
ØP	0.142	0.152	3.61	3.86	
Q	0.958	0.962	24.33	24.43	
R1	-	0.350	-	8.89	
R2	-	0.145	-	3.68	
S	0.570	0.590	14.48	14.99	

NOTES

1. Dimension does not include sealing flanges.
2. The outline contour is optional within zone defined by ØD and F1.

FIGURE 3 - FUNCTIONAL DIAGRAM



1. Emitter.
2. Base.
3. Collector.

NOTES

1. The collector is internally connected to the case.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply.

4. REQUIREMENTS

4.1 GENERAL

The complete requirements for procurement of the transistors specified herein are stated in this specification and ESA/SCC Generic Specification No. 5000. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

4.2.1 Deviations from Special In-process Controls

None.

4.2.2 Deviations from Final Production Tests (Chart II)

None.

4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)

(a) High Temperature Reverse Bias (H.T.R.B.) test: Not required.

4.2.4 Deviations from Qualification Tests (Chart IV)

None.

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the transistors specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the transistors specified herein shall be 6.4 grammes.

4.3.3 Terminal Strength

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The test conditions shall be as follows:-

Test Condition: 'A' (Tension).
Weight : 10lbs.
Duration: 15 second.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the transistors specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 Case

Metal case, hermetically sealed, similar to JEDEC TO-66.

4.4.2 Lead Material and Finish

The lead material shall be Type 'D' with Type '2' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500.

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

(a) Lead Identification.

(b) The SCC Component Number.

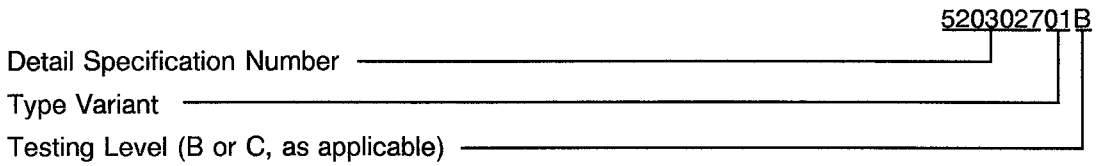
(c) Traceability Information.

4.5.2 Lead Identification

Lead identification shall be as shown in Figures 2 and 3.

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:-



4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.5.5 Marking of Small Components

When it is considered that the component is too small to accommodate the marking as specified above, as much as space permits shall be marked. The order of precedence shall be as follows:-

(a) Lead Identification.

(b) The SCC Component Number.

(c) Traceability Information.

The marking information in full shall accompany each component in its primary package.

4.6 ELECTRICAL MEASUREMENTS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured at room temperature are scheduled in Table 2. The measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3.

4.6.3 Circuits for Electrical Measurements

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for power burn-in shall be as specified in Table 5 of this specification.

4.7.3 Electrical Circuits for Burn-in

Circuits for use in performing the burn-in tests are shown in Figure 5 of this specification.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN	MAX	
1	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	3011	I_C = 100mA I_B = 0A Note 1	80	-	V
2	Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	3001	I_C = 100µA I_E = 0A Note 1	100	-	V
3	Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3026	I_C = 0A I_E = 1.0mA Note 1	6.0	-	V
4	Collector-Emitter Cut-off Current	I_{CEX}	3041	V_{CE} = 100V V_{BE} = − 1.5V	-	100	µA
		I_{CEO}	3041	V_{CE} = 80V I_B = 0A	-	700	µA
5	Collector-Base Cut-off Current	I_{CBO}	3036	V_{CB} = 100V I_E = 0A	-	100	µA
6	Emitter-Base Cut-off Current	I_{EBO}	3061	V_{EB} = 6.0V I_C = 0A	-	750	µA
7	D.C. Forward Current Transfer Ratio	h_{FE}	3076	I_C = 500mA V_{CE} = 5.0V Note 1	40	160	-
8	Collector Saturation Voltage	V_{CEsat}	3071	I_C = 1.0A I_B = 0.1A Notes 1 and 2	-	2.5	V
				I_C = 500mA I_B = 50mA Notes 1 and 2	-	1.0	V
9	Base Saturation Voltage	V_{BEsat}	3066	I_C = 2.5mA I_B = 0.25A Notes 1 and 2	-	1.5	V
				I_C = 5.0A I_B = 0.5A Notes 1 and 2	-	2.2	V

NOTES

1. Pulsed measurement: Pulse Width ≤300µs, Duty Cycle ≤2.0%.
2. Saturation voltages measured 6.0mm from header.

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN	MAX	
1	A.C. Forward Current Transfer Ratio	h_{fe}	3206	$I_C = 100mA$ $V_{CE} = 10V$ $f = 1.0kHz$	40	-	-
2	Output Capacitance	C_{obo}	3236	$V_{CB} = 10V$ $I_E = 0A$ $f = 100kHz$	-	50	pF
3	Current Gain Bandwidth Product	f_T	3261	$V_{CE} = 10V$ $I_C = 500mA$ $f = 10MHz$	10	-	MHz

FIGURE 4 - TEST CIRCUIT

Not applicable.

TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN	MAX	
1	Collector-Emitter Cut-off Current	I_{CEX}	3041	T_{amb} = +150°C V_{CE} = 100V V_{BE} = −1.5V	-	1.0	mA
2	D.C. Forward Current Transfer Ratio	h_{FE}	3076	T_{amb} = −55°C V_{CE} = 5.0V I_C = 500mA Note 1	20	-	-

NOTES

1. Pulsed measurement: Pulse Width ≤300μs, Duty Cycle ≤2.0%.

TABLE 4 - PARAMETER DRIFT VALUES

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
1	Collector-Emitter Cut-off Current	I_{CEX}	3041	V_{CE} = 100V V_{BE} = 1.5V	±20	μA
2	D.C. Forward Current Transfer Ratio	h_{FE}	3046	V_{CE} = 5.0V I_C = 500mA Note 1	±25	%
3	Collector Saturation Voltage	V_{CEsat}	3071	I_C = 500mA I_B = 50mA Note 1	±100	mV

NOTES

1. Pulsed measurement: Pulse Width ≤300μs, Duty Cycle ≤2.0%.

TABLE 5 - CONDITIONS FOR BURN-IN

No.	CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT
1	Ambient Temperature	T_{amb}	$+25 \pm 3$	°C
2	Collector-Base Voltage	V_{CB}	50 Note 1	V
3	Power Dissipation	P_{tot}	3.0	W

NOTES

1. No heat sink forced air directly on the device shall be permitted.

FIGURE 5 - ELECTRICAL CIRCUIT FOR BURN-IN

Not applicable.

4.8 ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC SPECIFICATION NO. 5000)

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 2. The measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.2 Electrical Measurements at Intermediate Points and on Completion of Endurance Tests

The parameters to be measured at intermediate points and on completion of endurance testing are scheduled in Table 6 of this specification.

4.8.3 Conditions for Operating Life Tests (Part of Endurance Testing)

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The conditions for operating life testing shall be the same as specified in Table 5 for the burn-in test.

4.8.4 Electrical Circuits for Operating Life Tests

The circuit to be used for performance of the operating life tests shall be the same as shown in Figure 5 for burn-in.

4.8.5 Conditions for High Temperature Storage Test (Part of Endurance Testing)

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 5000. The temperature to be applied shall be the maximum storage temperature specified in Table 1(b) of this specification.

TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

No.	CHARACTERISTICS	SYMBOL	MIL-STD-750 TEST METHOD	TEST CONDITIONS	LIMITS		UNIT
					MIN.	MAX.	
1	D.C. Forward Current Transfer Ratio	h_{FE}	3076	$I_C = 500mA$ $V_{CE} = 5.0V$ Note 1	40	160	-
2	Collector Saturation Voltage	V_{CEsat}	3071	$I_C = 500mA$ $I_B = 50mA$ Note 1	-	1.0	V
6	Collector-Emitter Cut-off Current	I_{CEX}	3041	$V_{BE} = -1.5V$ $V_{CE} = 100V$ Note 1	-	100	µA

NOTES

1. Pulsed measurement: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2.0\%$.